



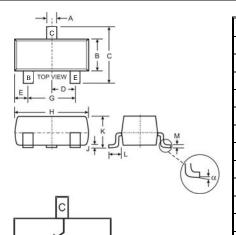
# BC807-16/ -25/ -40

#### **Features**

- Ideally Suited for Automatic Insertion
- **Epitaxial Planar Die Construction**
- For Switching, AF Driver and Amplifier Applications
- Complementary NPN Types Available (BC817)
- Lead Free/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Pin Connections: See Diagram
- Ordering Information: See Page 3
- Marking Information: See Page 3
  - BC807-16 5A, K5A
  - BC807-25 5B, K5B
  - BC807-40 5C, K5C
- Weight: 0.008 grams (approximate)



	SOT-23										
Dim	Min	Max									
Α	0.37	0.51									
В	1.20	1.40									
С	2.30	2.50									
D	0.89	1.03									
E	0.45	0.60									
G	1.78	2.05									
Н	2.80	3.00									
J	0.013	0.10									
K	0.903	1.10									
L	0.45	0.61									
М	0.085	0.180									
α	0°	8°									
All Din	nensions	in mm									

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current	Ic	-500	mA
Peak Collector Current	I <sub>CM</sub>	-1000	mA
Peak Emitter Current	I <sub>EM</sub>	-1000	mA
Power Dissipation at T <sub>SB</sub> = 50°C (Note 1)	P <sub>d</sub>	310	mW
Thermal Resistance, Junction to Substrate Backside (Note 1)	$R_{ heta JSB}$	320	°C/W
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{ heta JA}$	403	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150	°C

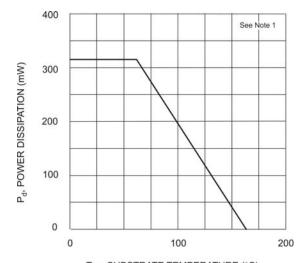
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	(Note 2)	Symbol	Min	Тур	Max	Unit	Test Condition
DC Current Gain	Current Gain Group -16 -25 -40 Current Gain Group -16 -25 -40	h <sub>FE</sub>	100 160 250 60 100 170	_	250 400 600 — —	_	$V_{CE} = 1.0V, I_{C} = 100 \text{mA}$ $V_{CE} = 1.0V, I_{C} = 300 \text{mA}$
Collector-Emitter Saturation Voltage		V <sub>CE(SAT)</sub>	_	_	-0.7	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Voltage		$V_{BE}$	_	_	-1.2	V	$V_{CE} = 1.0V, I_{C} = 300mA$
Collector-Emitter Cutoff Current		I <sub>CES</sub>	_	_	-100 -5.0	nΑ μΑ	$V_{CE} = 45V$ $V_{CE} = 25V$ , $T_j = 150$ °C
Emitter-Base Cutoff Current		I <sub>EBO</sub>	_	_	-100	nA	V <sub>EB</sub> = 4.0V
Gain Bandwidth Product		f⊤	100	_	_	MHz	$V_{CE} = 5.0V, I_{C} = 10mA,$ f = 50MHz
Collector-Base Capacitance		C <sub>CBO</sub>	_	_	12	pF	$V_{CB} = 10V, f = 1.0MHz$

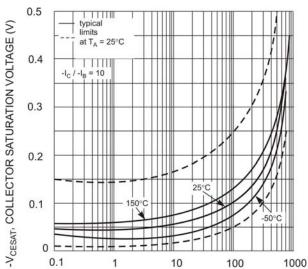
1. Device mounted on ceramic substrate 0.7mm; 2.5cm<sup>2</sup> area. Notes:

- Short duration pulse test used to minimize self-heating effect.
- No purposefully added lead.

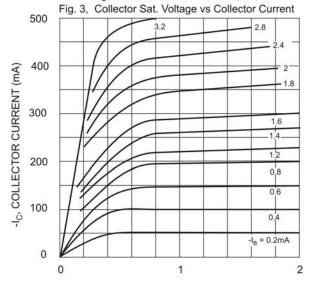




T<sub>SB</sub>, SUBSTRATE TEMPERATURE (°C) Fig. 1, Power Derating Curve



-I<sub>C</sub>, COLLECTOR CURRENT (mA)



 $\hbox{-V}_{\text{CE}}, \hbox{COLLECTOR-EMITTER VOLTAGE (V)} \\ \hbox{Fig. 5, Typical Emitter-Collector Characteristics} \\$ 

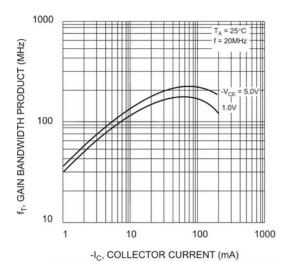
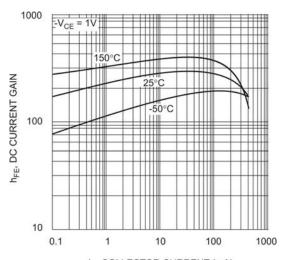
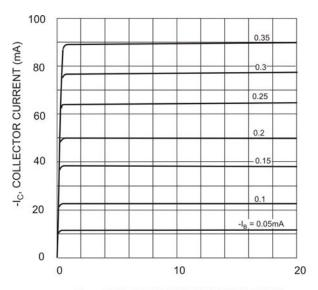


Fig. 2, Gain-Bandwidth Product vs Collector Current



-I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 4, DC Current Gain vs Collector Current



 $-V_{CE}$ , COLLECTOR-EMITTER VOLTAGE (V) Fig. 6, Typical Emitter-Collector Characteristics



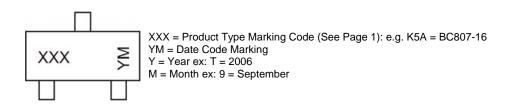
#### **Ordering Information** (Note 4)

Device*	Packaging	Shipping
BC807-xx-7-F	SOT-23	3000/Tape & Reel

xx = gain group, eg. BC807-16-7-F.

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**



Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z

	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Ī	Code	1	2	3	4	5	6	7	8	9	0	N	D

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